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1 Electrical ratings

Symbol	Dovometov	Value			Unit
Symbol	Parameter	TO-247 TO-220FP		TO-3PF	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)		600		V
Ι _C	Continuous collector current at $T_C = 25$ °C	60	19	36	A
Ι _C	Continuous collector current at $T_C = 100$ 35121		18	A	
$I_{CP}^{(1)}$	Pulsed collector current	150		Α	
I _{CL} ⁽²⁾	Turn-off latching current	80			А
V_{GE}	Gate-emitter voltage		± 20		V
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; Tc = 25 °C)		2500		v
P _{TOT}	Total dissipation at $T_C = 25 \ ^{\circ}C$	200	40	88	W
T _{stg}	Storage temperature	- 55 to 150		ာ့	
Тj	Operating junction temperature				

Table 2.Absolute maximum ratings

1. Pulse width limited by maximum junction temperature and turn-off within RBSOA

2. V_{CLAMP} = 80% (V_{CES}), V_{GE} = 15 V, R_G = 10 Ω , T_J = 150 °C

Symbol	Parameter		Value		Unit
Symbol	Falameter	ТО-247 ТО-220FP ТО-3Р		TO-3PF	Onit
R _{thj-case}	Thermal resistance junction-case	0.63	3.1	1.41	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	50	62.5	50	°C/W



2 Electrical characteristics

 $(T_J = 25 \ ^{\circ}C \text{ unless otherwise specified})$

Table 4.	Static
	Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage (V _{GE} = 0)	I _C = 1 mA	600			V
V	Collector-emitter	V _{GE} = 15 V, I _C = 20 A		2	2.5	v
V _{CE(sat)}	saturation voltage	V _{GE} = 15V, I _C = 20 A,T _J = 125 °C		1.65		v
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1 \text{ mA}$	3.75		5.75	V
lana	Collector cut-off current	V _{CE} = 600 V			250	μA
ICES	(V _{GE} = 0)	V _{CE} = 600 V, T _J = 125 °C			1	mA
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	$V_{GE} = \pm 20 V$			± 100	nA

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0	-	2400 235 50	-	pF pF pF
Q _g Q _{ge} Q _{gc}	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 400 \text{ V}, I_C = 20 \text{ A},$ $V_{GE} = 15 \text{ V},$ (see Figure 18)	-	140 13 52	-	nC nC nC



	entening enten (inductive lodd)					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 400 \text{ V}, I_C = 20 \text{ A}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V},$ (see Figure 17)	-	30 15 1650	-	ns ns A/µs
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 400 \text{ V}, I_C = 20 \text{ A}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_J = 125 \text{ °C} (see Figure 17)$	-	30 15 1600	-	ns ns A/µs
$t_r(V_{off}) \ t_d(_{off}) \ t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 400 \text{ V}, I_{C} = 20 \text{ A},$ $R_{GE} = 10 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17)	-	30 175 40	-	ns ns ns
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 400 \text{ V}, I_C = 20 \text{ A},$ $R_{GE} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_J = 125 \text{ °C}$ <i>(see Figure 17)</i>	-	50 225 70	-	ns ns ns

Table 6. Switching on/off (inductive load)

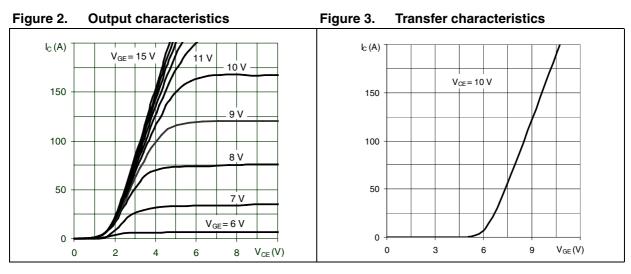
Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E _{on} ⁽¹⁾	Turn-on switching losses	$V_{CC} = 400 \text{ V}, I_{C} = 20 \text{ A}$		290		μJ
E _{off}	Turn-off switching losses	$R_{G} = 10 \Omega$, $V_{GE} = 15 V$,	-	185		μJ
E _{ts}	Total switching losses	(see Figure 19)		475		μJ
E _{on} ⁽¹⁾	Turn-on switching losses	$V_{CC} = 400 \text{ V}, I_{C} = 20 \text{ A}$		420		μJ
E _{off}	Turn-off switching losses	R_{G} = 10 Ω, V_{GE} = 15 V,	-	350	530	μJ
E _{ts}	Total switching losses	T _J = 125 °C <i>(see Figure 19)</i>		770		μJ

1. Eon is the turn-on losses when a typical diode is used in the test circuit in *Figure 19*. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature (25 °C and 125 °C). Eon includes diode recovery energy.



Electrical characteristics (curves) 2.1





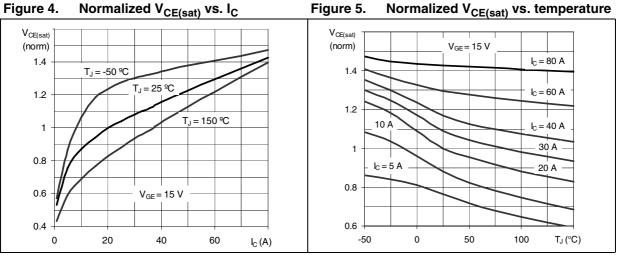
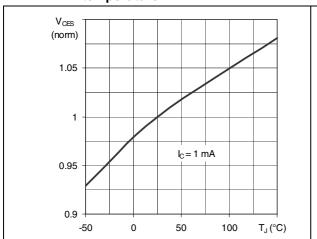
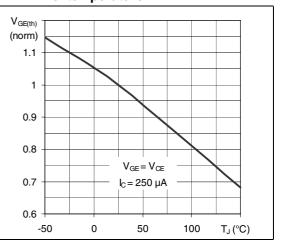


Figure 6. Normalized breakdown voltage vs. Figure 7. temperature



Normalized gate threshold voltage vs. temperature

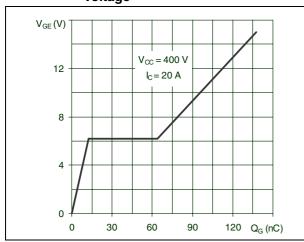


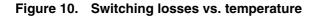
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Figure 8. Gate charge vs. gate-emitter voltage





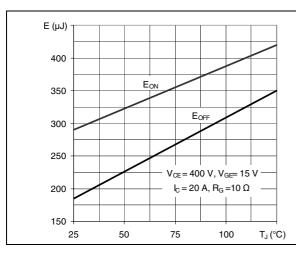


Figure 12. Switching losses vs. collector current

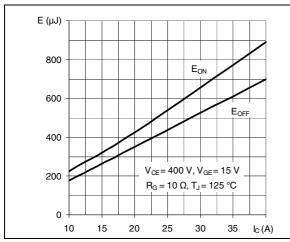


Figure 9. Capacitance variations

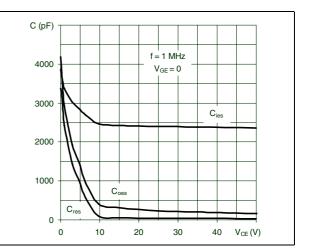
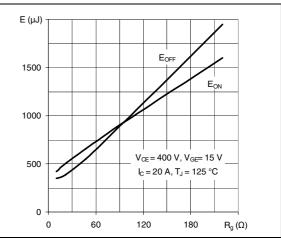
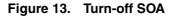
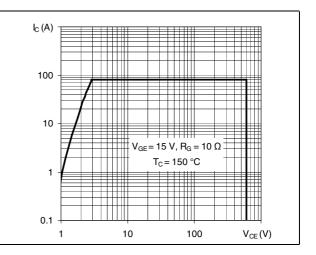


Figure 11. Switching losses vs. gate resistance







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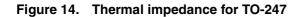


Figure 15. Thermal impedance for TO-220FP

10-1

0.05

0.01

10-2

 $\delta = t_p / \tau$

100

 $Z_{th} = k R_{thJ-c}$

10¹

 $\delta = 0.5$

0.2

0.1

TII

10-4

SINGLE PULSE

10-3

к

10 -

10 -2

10⁻³

тогрјк

† p (s)

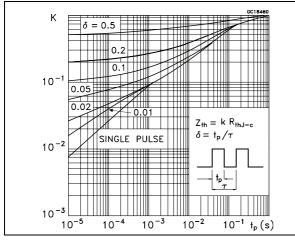
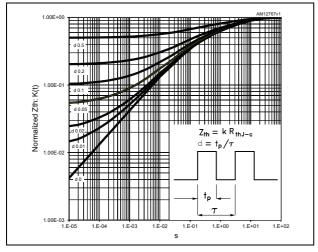


Figure 16. Thermal impedance for TO-3PF





3 Test circuits

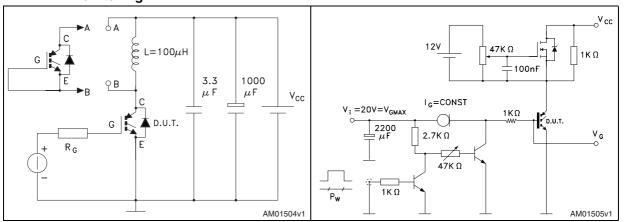
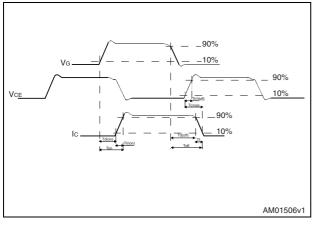


Figure 18. Gate charge test circuit

Figure 17. Test circuit for inductive load switching

Figure 19. Switching waveform





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

Dim		mm	
Dim.	Min.	Тур.	Max.
А	4.4		4.6
В	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Table 8.	TO-220FP	mechanical data





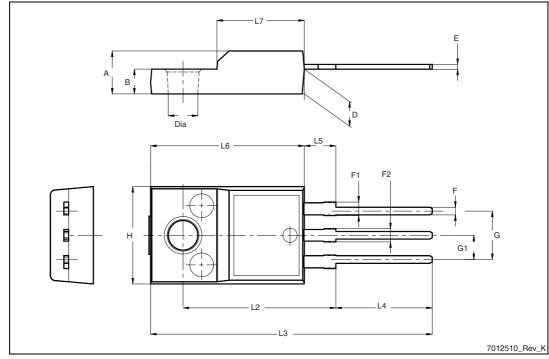


Figure 20. TO-220FP drawing



Dim		mm	
Dim.	Min.	Тур.	Max.
Α	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Table 9.TO-247 mechanical data

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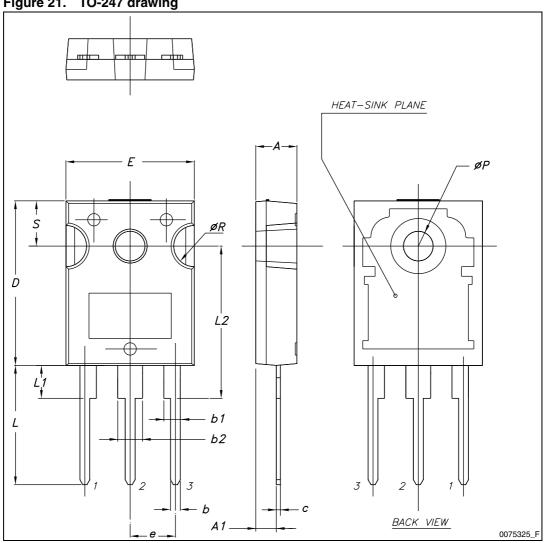


Figure 21. TO-247 drawing



Dim.	mm		
	Min.	Тур.	Max.
А	5.30		5.70
С	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
Н	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
Ν	1.80	1.80 2.20	
R	3.80		4.20
Dia	3.40		3.80

Table 10.TO-3PF mechanical data



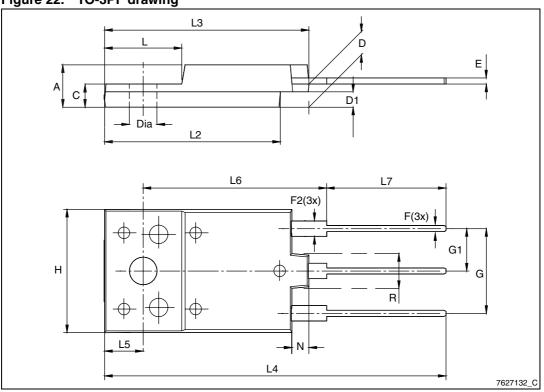


Figure 22. TO-3PF drawing



5 Revision history

Table 11.Document revision history

Date	Revision	Changes	
17-May-2010	1	Initial release.	
14-Dec-2010	2	2 Document status promoted from preliminary data to datasheet. Inserted new order code STGF35HF60W in TO-220FP package.	
24-Jul-2012	3	Inserted new order code STGFW35HF60W in TO-3PF package.	



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